



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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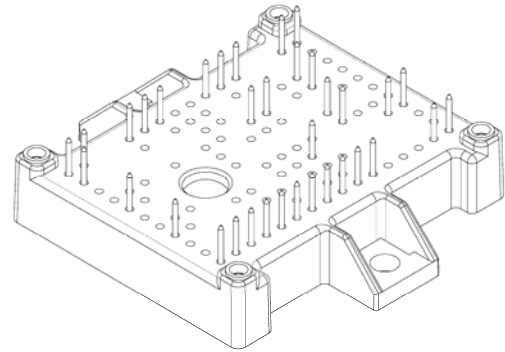
GCMS080A120B3C1

1.2kV 80 mohm SiC MOSFET 6-Pack Module



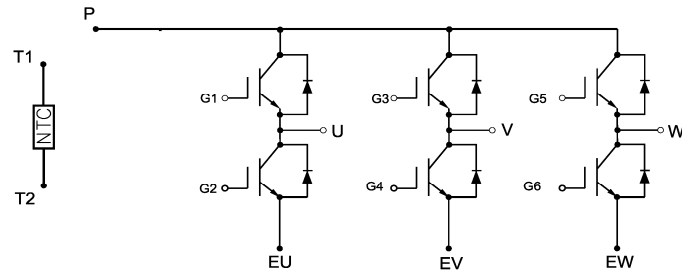
Features:

- Ultra Low Loss
- High-Frequency Operation
- Zero Reverse Recovery Current from SiC SBDs
- Small Turn-off Tail Current from SiC MOSFETs
- Normally-off Device Operation
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Industrial Motor Drivers
- Solar Inverters
- UPS and SMPS
- Three-Phase PFC



Maximum Rated Values ($T_C=25^{\circ}\text{C}$ Unless otherwise specified)

| Parameters | Symbol | Conditions | Specifications | Units |
|----------------------------------|-----------|---|----------------|--------------------|
| Drain - Source Voltage | V_{DS} | | 1200 | V |
| Continuous Drain Current (Q1-Q4) | I_D | $V_{GS}=20\text{V}, T_C = 25^{\circ}\text{C}$ | 40 | A |
| | | $V_{GS}=20\text{V}, T_C = 80^{\circ}\text{C}$ | 20 | A |
| Gate - Source Voltage | V_{GS} | | +25/-10 | V |
| Pulsed Drain Current | I_{DS} | Limited by T_{j_max} | 60 | A |
| Maximum Power Dissipation | P_D | $T_C = 25^{\circ}\text{C}$ | 220 | W |
| | | $T_C = 100^{\circ}\text{C}$ | TBD | W |
| Operating Junction Temperature | T_j | | -40 ~ +150 | $^{\circ}\text{C}$ |
| Storage Temperature | T_{STG} | | -40 ~ +125 | $^{\circ}\text{C}$ |
| Solder Temperature | T_L | Max for 10 sec | 260 | $^{\circ}\text{C}$ |

Electrical Characteristics of MOSFETs ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

| Parameters | Symbol | Conditions | Min | Typ | Max | Units |
|---------------------------------|---------------|--|-----|------|-----------|------------------|
| OFF | | | | | | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 1200\text{V}, V_{GS} = 0\text{V}$ | -- | 1 | 100 | μA |
| Gate-Source Leakage Current | I_{GSS} | $V_{DS} = 0\text{V}, V_{GS} = 20\text{V}$ | -- | -- | ± 250 | nA |
| ON | | | | | | |
| Gate-Source Threshold Voltage | $V_{GS(TH)}$ | $V_{DS} = 10\text{V}, I_D = 1\text{mA}$ | 1.7 | 2.2 | -- | V |
| On State Resistance | $R_{DS(ON)}$ | $V_{GS} = 20\text{V}, I_D = 20\text{A}, T_j = 25^{\circ}\text{C}$ | -- | 80 | -- | $\text{m}\Omega$ |
| | | $V_{GS} = 20\text{V}, I_D = 20\text{A}, T_j = 150^{\circ}\text{C}$ | -- | 150 | -- | $\text{m}\Omega$ |
| DYNAMIC | | | | | | |
| Input Capacitance | C_{ISS} | $V_{DS} = 800\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$ | -- | 950 | -- | pF |
| Output Capacitance | C_{OSS} | | -- | 80 | -- | pF |
| Reverse Transfer Capacitance | C_{RSS} | | -- | 6.5 | -- | pF |
| Module Stray Inductance | L_{\square} | | -- | TBD | -- | nH |
| Module Lead Resistance | R_{mod} | | -- | TBD | -- | $\text{m}\Omega$ |
| SWITCHING | | | | | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 800\text{V}, I_D = 20\text{A}$ $R_G = 2.5\Omega, V_{GS} = -5/20\text{V}$ Inductive Load, $T_j = 25^{\circ}\text{C}$ | -- | 15 | -- | ns |
| Rise Time | t_r | | -- | 35 | -- | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | -- | 32 | -- | ns |
| Fall Time | t_f | | -- | 26 | -- | ns |
| Turn-On Switching Energy Loss | E_{ON} | | -- | 0.4 | -- | mJ |
| Turn-Off Switching Energy Loss | E_{OFF} | | -- | 0.25 | -- | mJ |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 800\text{V}, I_D = 20\text{A}$ $R_G = 2.5\Omega, V_{GS} = -5/20\text{V}$ Inductive Load, $T_j = 125^{\circ}\text{C}$ | -- | TBD | -- | ns |
| Rise Time | t_r | | -- | TBD | -- | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | -- | TBD | -- | ns |
| Fall Time | t_f | | -- | TBD | -- | ns |
| Turn-On Switching Energy Loss | E_{ON} | | -- | TBD | -- | mJ |
| Turn-Off Switching Energy Loss | E_{OFF} | | -- | TBD | -- | mJ |
| Total Gate Charge | Q_G | $V_{DD} = 800\text{V}, I_D = 20\text{A}$ $V_{GS} = -5/20\text{V}$ | -- | 49.2 | -- | nC |
| Gate-Source Charge | Q_{GS} | | -- | 10.8 | -- | nC |
| Gate-Drain Charge | Q_{GD} | | -- | 18 | -- | nC |
| Short Circuit Withstanding Time | t_{sc} | $V_{CC} = 800\text{V}, V_{GS} = 20\text{V}$ $T_j = 125^{\circ}\text{C}$ | TBD | -- | -- | μs |

SiC Freewheeling Diode Characteristics

| Parameters | Symbol | Conditions | Min | Typ | Max | Units |
|---|----------|--|-----|-----|-----|-------|
| Max continuous drain-source diode forward current | I_S | | | 20 | | A |
| Max pulsed drain-source diode forward current | I_{SM} | | | 60 | | A |
| Diode forward voltage | V_{SD} | $V_{GS}=-5V, I_{SD}=20A$ | | 1.7 | | V |
| Reverse recovery charge | Q_C | $V_{GS}=-5V, I_{SD}=20A, T_j=25^\circ C$ | | 102 | | nC |

Thermal Characteristics

| Parameters | Symbol | Conditions | Min | Typ | Max | Units |
|---|------------|------------------|-----|------|-----|--------------|
| Thermal Resistance Junction to Case: MOSFET | R_{thJM} | $T_C=80^\circ C$ | | 0.59 | | $^\circ C/W$ |
| Thermal Resistance Junction to Case: SBD | R_{thJD} | $T_C=80^\circ C$ | | 1.13 | | $^\circ C/W$ |

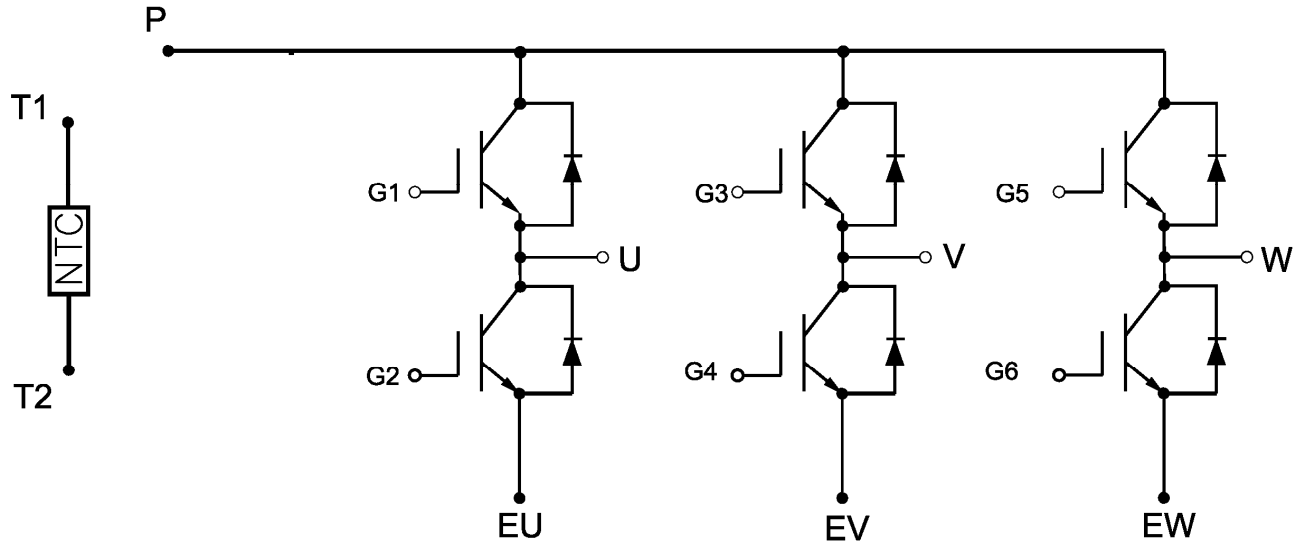
Internal NTC-Thermistor Characteristic

| Symbol | Description | Min | Typ | Max | Unit |
|--------------|---|-----|------|---------|------------|
| R_{25} | $T_C = 25^\circ C$ | | 5 | | k Ω |
| $\Delta R/R$ | $T_C = 100^\circ C, R_{100} = 481\Omega$ | | | ± 5 | % |
| P_{25} | $T_C = 25^\circ C$ | | 50 | | mW |
| $B_{25/50}$ | $R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298.15K))]$ | | 3380 | | K |
| $B_{25/80}$ | $R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298.15K))]$ | | 3440 | | K |

Module

| Symbol | Description | Min | Typ | Max | Unit |
|-----------------|--|-----|------|------|--------------|
| V_{iso} | Isolation Voltage(All Terminals Shorted) | | | 2500 | V |
| | $f = 50Hz, 1minute$ | | | | |
| T_{JOP} | Maximum Operating Junction Temperature Range | -40 | | +150 | $^\circ C$ |
| T_{stg} | Storage Temperature | -40 | | +125 | $^\circ C$ |
| $R_{\theta CS}$ | Case-To-Sink (Conductive Grease Applied) | | 0.05 | | $^\circ C/W$ |
| T | Mounting Screw:M4 | 1.0 | | 1.5 | N·m |
| G | Weight | | 40 | | g |

Internal Circuit:



Revision History

| Date | Revision | Notes |
|-----------|----------|-----------------|
| 9/30/2016 | 1.0 | Initial release |
| | | |
| | | |

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Notes

- RoHS Compliance**
 The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.gptechgroup.com.
- REACH Compliance**
 REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at GPTG Headquarters in Lake Forest, California to insure you get the most up-to-date REACH SVHC Declaration.
 REACH banned substance information (REACH Article 67) is also available upon request.
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